



QFET®

FQP45N15V2/FQPF45N15V2

150V N-Channel MOSFET

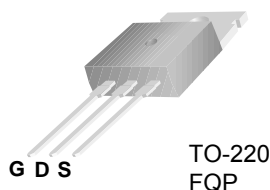
General Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

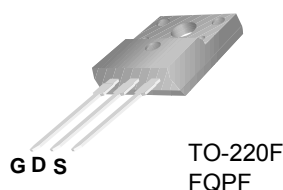
This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for DC to DC converters, synchronous rectification, and other applications lowest Rds(on) is required.

Features

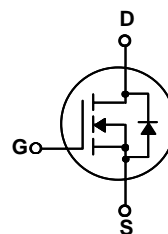
- 45A, 150V, $R_{DS(on)} = 0.04\Omega$ @ $V_{GS} = 10V$
- Low gate charge (typical 72 nC)
- Low Crss (typical 135 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



TO-220
FQP



TO-220F
FQPF



Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter	FQP45N15V2	FQPF45N15V2	Units
V _{DSS}	Drain-Source Voltage	150		V
I _D	Drain Current - Continuous (T _C = 25°C)	45	45 *	A
	- Continuous (T _C = 100°C)	31	31 *	A
I _{DM}	Drain Current - Pulsed (Note 1)	180	180 *	A
V _{GSS}	Gate-Source Voltage	± 30		V
E _{AS}	Single Pulsed Avalanche Energy (Note 2)	1124		mJ
I _{AR}	Avalanche Current (Note 1)	45		A
E _{AR}	Repetitive Avalanche Energy (Note 1)	22		mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.5		V/ns
P _D	Power Dissipation (T _C = 25°C)	220	66	W
	- Derate above 25°C	1.47	0.44	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +150		°C
T _L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300		°C

* Drain current limited by maximum junction temperature

Thermal Characteristics

Symbol	Parameter	FQP45N15V2	FQPF45N15V2	Units
R _{θJC}	Thermal Resistance, Junction-to-Case	0.68	2.25	°C/W
R _{θCS}	Thermal Resistance, Case-to-Sink Typ.	0.5	--	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient	62.5	62.5	°C/W

FQP45N15V2/FQPF45N15V2

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	150	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, Referenced to 25°C	--	0.21	--	V/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 150\text{ V}, V_{GS} = 0\text{ V}$	--	--	1	μA
		$V_{DS} = 120\text{ V}, T_C = 150^\circ\text{C}$	--	--	10	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2.0	--	4.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 22.5\text{ A}$	--	0.034	0.04	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 40\text{ V}, I_D = 22.5\text{ A}$ (Note 4)	--	40	--	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	2330	3030	pF
C_{oss}	Output Capacitance		--	510	670	pF
C_{rss}	Reverse Transfer Capacitance		--	135	176	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 75\text{ V}, I_D = 45\text{ A},$ $R_G = 25\text{ }\Omega$ (Note 4, 5)	--	22	54	ns
t_r	Turn-On Rise Time		--	232	474	ns
$t_{d(off)}$	Turn-Off Delay Time		--	224	458	ns
t_f	Turn-Off Fall Time		--	246	502	ns
Q_g	Total Gate Charge	$V_{DS} = 120\text{ V}, I_D = 45\text{ A},$ $V_{GS} = 10\text{ V}$ (Note 4, 5)	--	72	94	nC
Q_{gs}	Gate-Source Charge		--	13	--	nC
Q_{gd}	Gate-Drain Charge		--	31	--	nC

Drain-Source Diode Characteristics and Maximum Ratings

I _S	Maximum Continuous Drain-Source Diode Forward Current		--	--	45	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	180	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 45 A	--	--	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 45 A, dI _F / dt = 100 A/μs (Note 4)	--	176	--	ns
Q _{rr}	Reverse Recovery Charge		--	1.19	--	μC

Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. $L = 0.74\text{ mH}$, $I_{AS} = 45\text{ A}$, $V_{DD} = 50\text{ V}$, $R_G = 25\text{ }\Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 45\text{ A}$, $di/dt \leq 200\text{ A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$
5. Essentially independent of operating temperature

Typical Characteristics

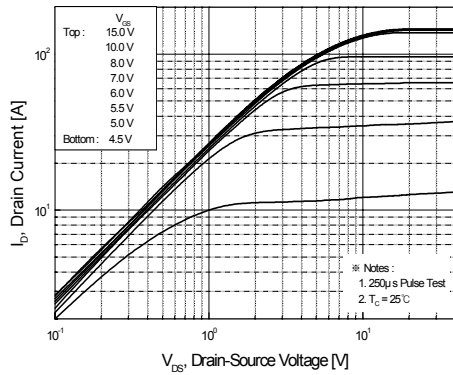


Figure 1. On-Region Characteristics

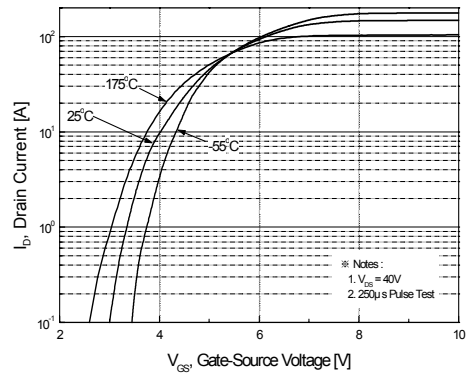


Figure 2. Transfer Characteristics

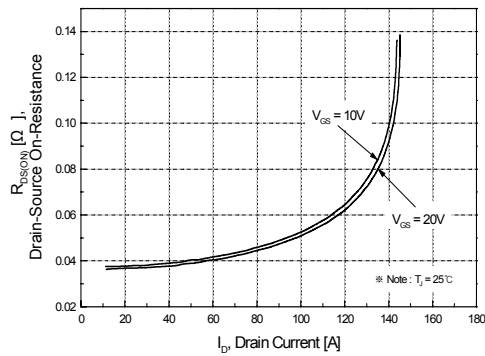


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

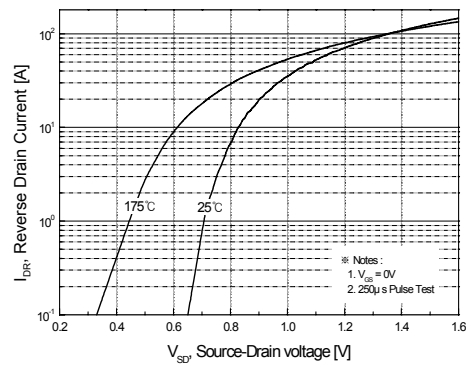


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

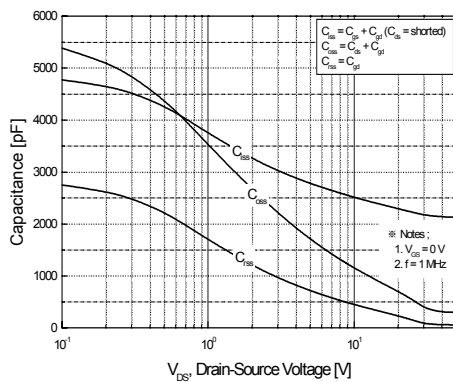


Figure 5. Capacitance Characteristics

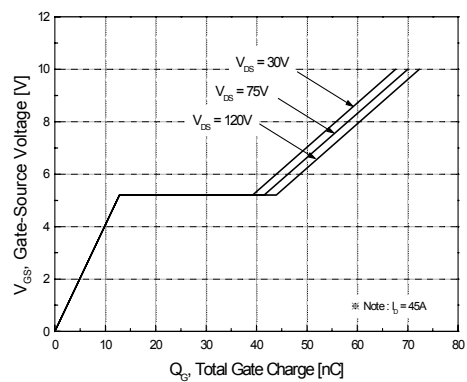


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

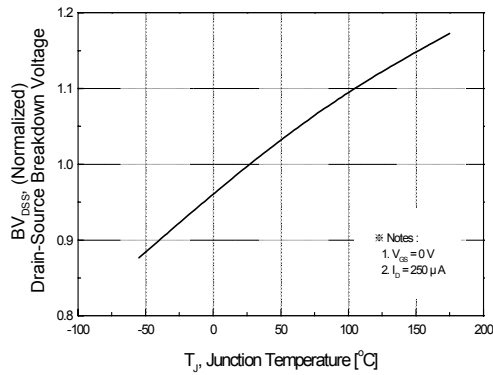


Figure 7. Breakdown Voltage Variation vs Temperature

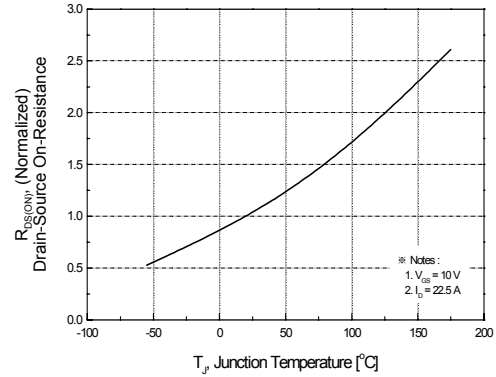


Figure 8. On-Resistance Variation vs Temperature

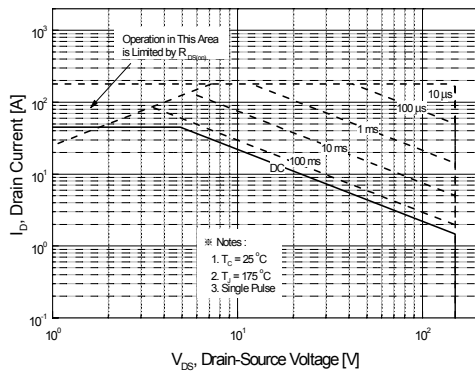


Figure 9-1. Maximum Safe Operating Area for FQP45N15V2

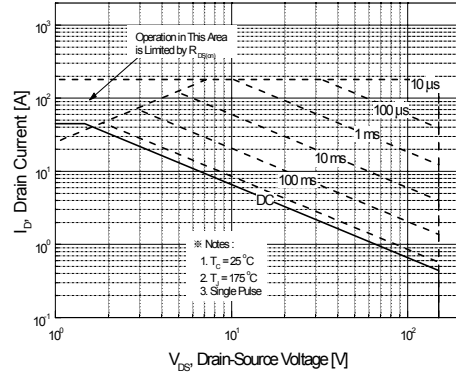


Figure 9-2. Maximum Safe Operating Area for FQPF45N15V2

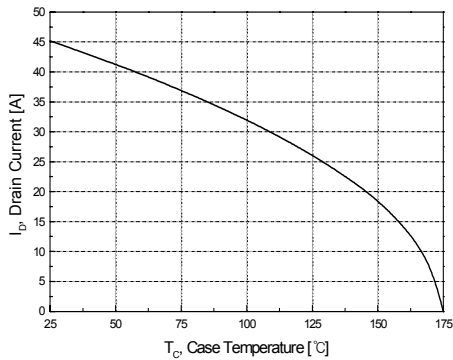


Figure 10. Maximum Drain Current vs Case Temperature

Typical Characteristics (Continued)

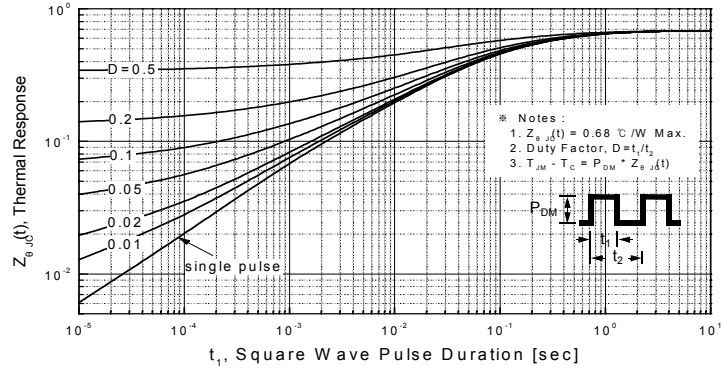


Figure 11. Transient Thermal Response Curve for FQP45N15V2

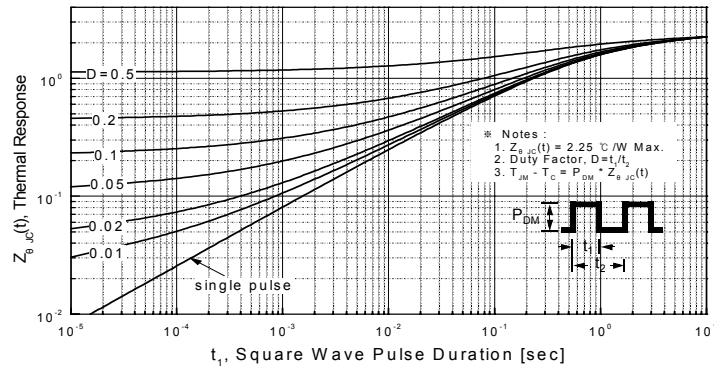
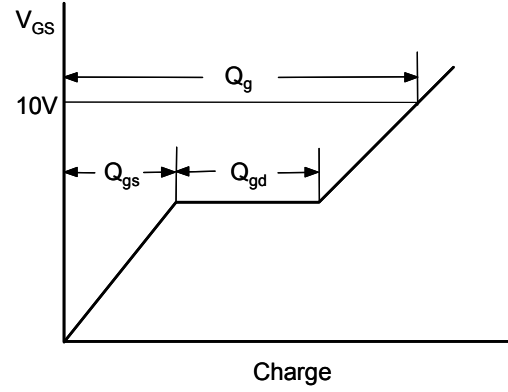
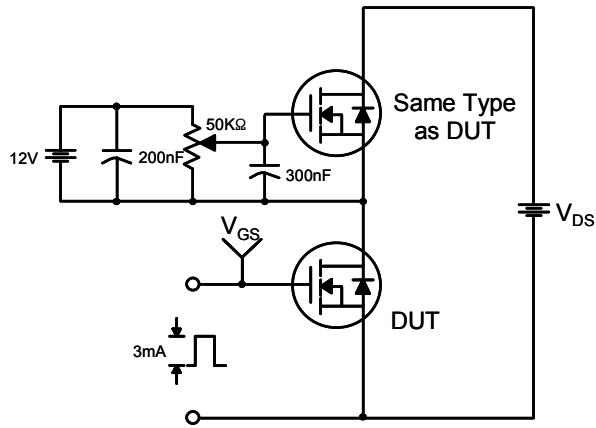
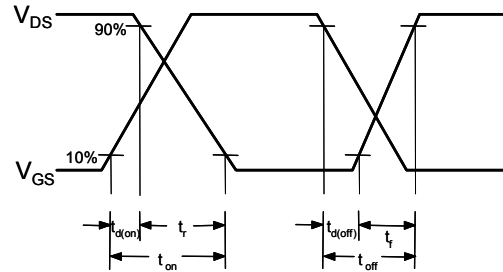
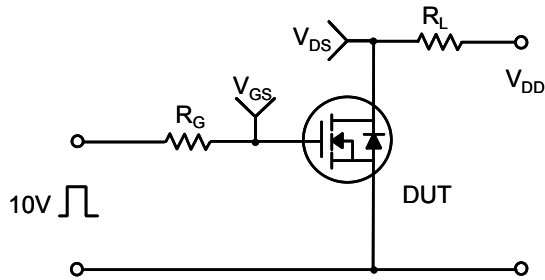


Figure 11-2. Transient Thermal Response Curve for FQPF45N15V2

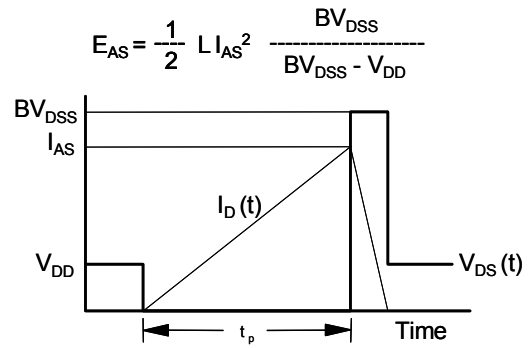
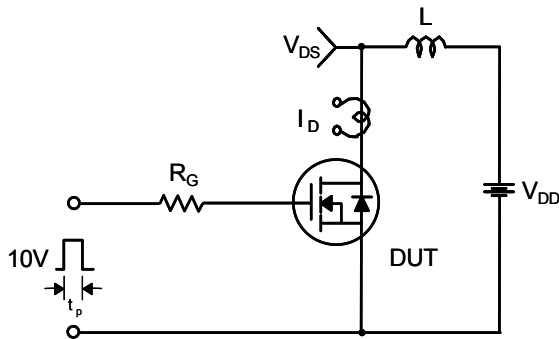
Gate Charge Test Circuit & Waveform



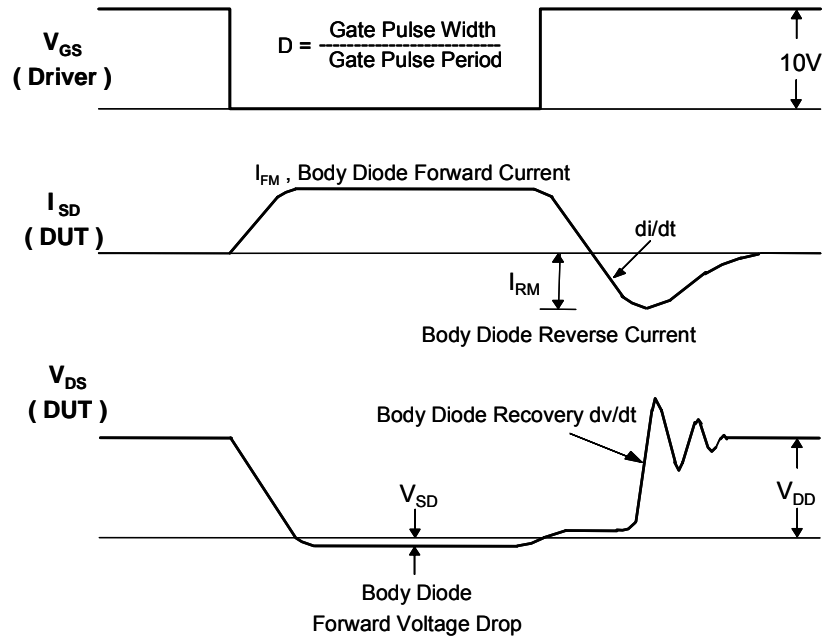
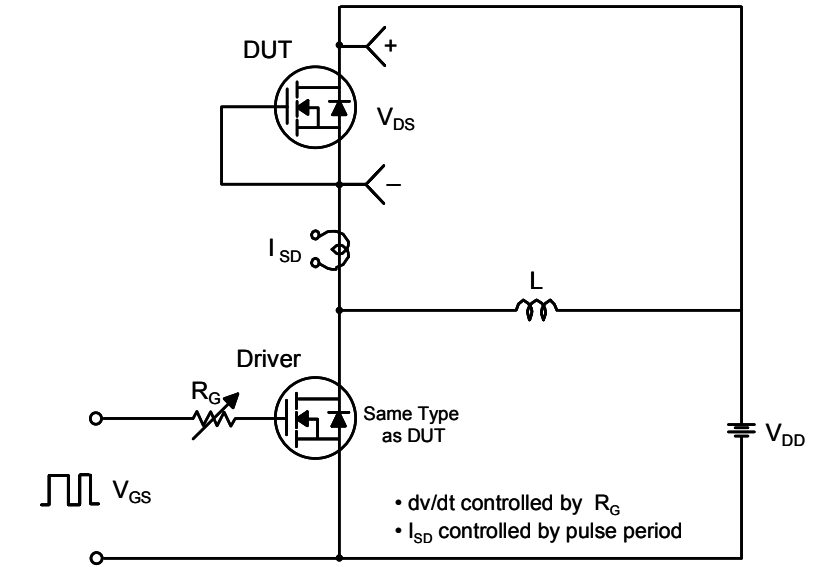
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms

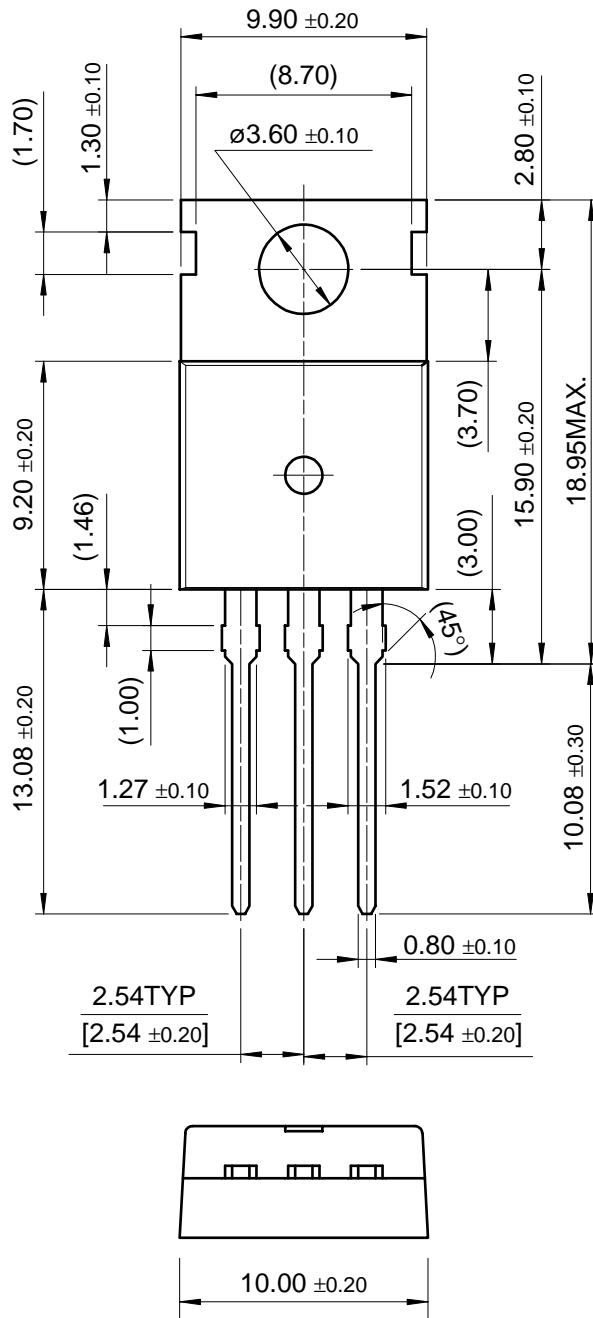


Peak Diode Recovery dv/dt Test Circuit & Waveforms



Package Dimensions

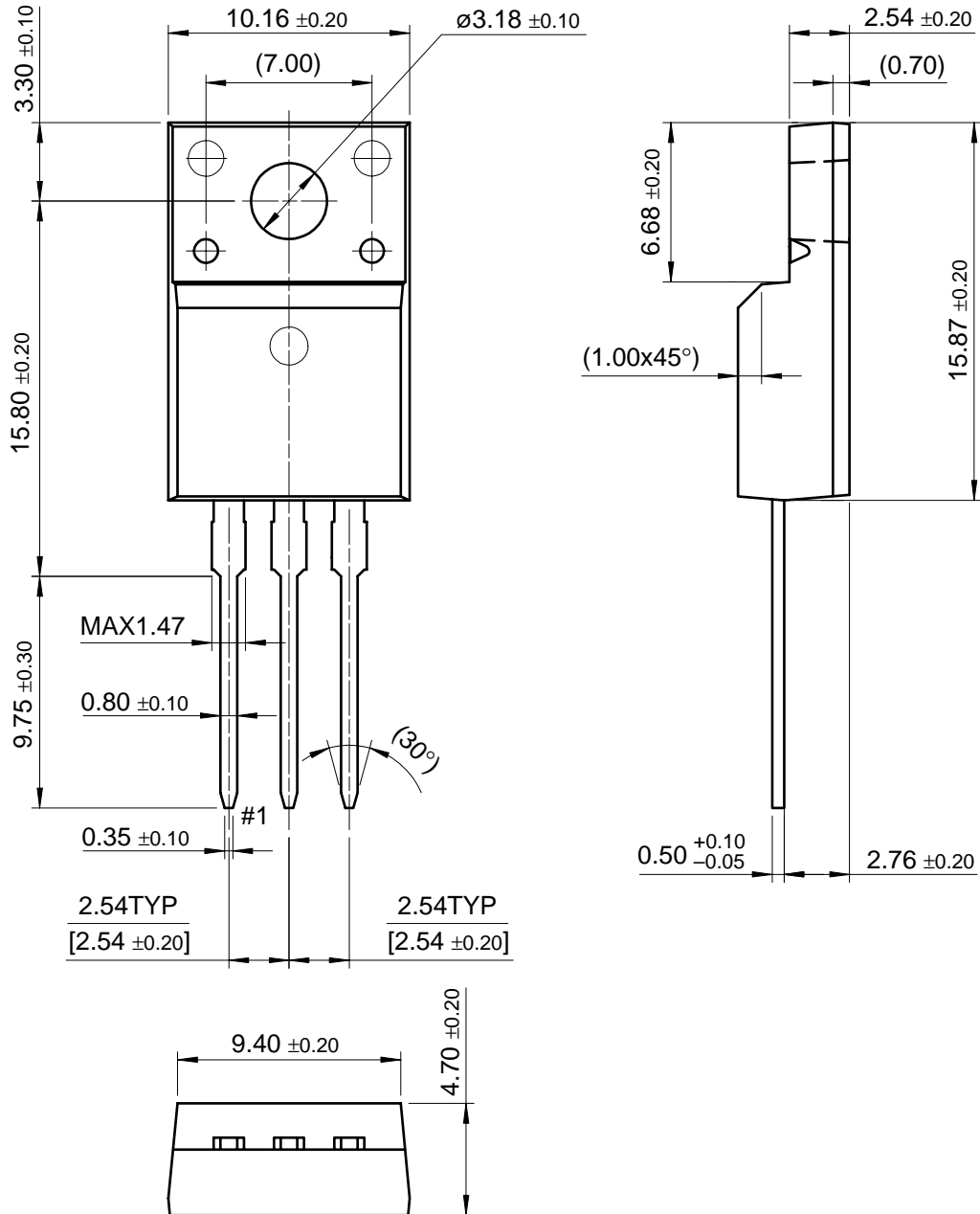
TO-220



Dimensions in Millimeters

Package Dimensions (Continued)

TO-220F



Dimensions in Millimeters

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CROSSVOLT™	GlobalOptoisolator™	MicroPak™	QFET [®]	SuperSOT™-8
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